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Diodes Incorporated 2N7002DW-7

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Datasheet of 2N7002DW-7 - MOSFET 2N-CH 60V 0.23A SOT-363

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2N7002DW

DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

| V _{(BR)DSS} | R _{DS(ON)} max | I _D max T _A = +25°C |
|----------------------|-----------------------------|--|
| 60V | 7.5Ω @ V _{GS} = 5V | 0.23A |

Description

This MOSFET has been designed to minimize the on-state resistance $(R_{DS(ON)})$ and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Motor Control
- Power Management Functions

Features

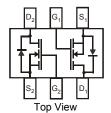
- Dual N-Channel MOSFET
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- · Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Notes 3 & 4)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT363
- Case Material: Molded Plastic. "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020



· Weight: 0.006 grams (approximate)



Internal Schematic

SOT363



Top View

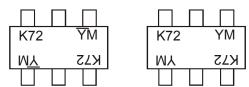
Ordering Information (Note 5)

| Part Number | Compliance | Case | Packaging |
|----------------|------------|--------|--------------------|
| 2N7002DW-7-F | Standard | SOT363 | 3,000/Tape & Reel |
| 2N7002DWQ-7-F | Automotive | SOT363 | 3,000/Tape & Reel |
| 2N7002DW-13-F | Standard | SOT363 | 10,000/Tape & Reel |
| 2N7002DWQ-13-F | Automotive | SOT363 | 10,000/Tape & Reel |

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Product manufactured with Date Code UO (week 40, 2007) and newer are built with Green Molding Compound. Product manufactured prior to Date Code UO are built with Non-Green Molding Compound and may contain Halogens or Sb₂O₃ Fire Retardants.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



K72 = Product Type Marking Code

YM = Date Code Marking for SAT (Shanghai Assembly/ Test site)

YM = Date Code Marking for CAT (Chengdu Assembly/ Test site)

Y or \overline{Y} = Year (ex: A = 2013)

M = Month (ex: 9 = September)

Date Code Key

| Year | 1998 | 1999 | 2000 | 2001 | 2002 | 2003 | 2004 | | 2011 | 2012 | 2013 | 2014 | 2015 | 2016 | 2017 |
|-------|------|------|------|------|------|------|------|---|------|------|------|------|------|------|------|
| Code | J | K | L | М | N | Р | R | | Υ | Z | Α | В | С | D | Е |
| Month | Jan | Fel | b | Mar | Apr | May | Ju | n | Jul | Aug | Sep | Oc | t | Nov | Dec |
| Code | 1 | 2 | | 3 | 4 | 5 | 6 | | 7 | 8 | 9 | 0 | | N | D |



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| Characteristic | | Symbol | Value | Units | |
|--|--|-----------|----------------|----------------------|---|
| Drain-Source Voltage | | V_{DSS} | 60 | V | |
| Drain-Gate Voltage $R_{GS} \le 1.0 M\Omega$ | V_{DGR} | 60 | V | | |
| Gate-Source Voltage | Continuous | | V_{GSS} | ±20 | V |
| Gate-Source Voltage | Pulsed | | V_{GSS} | ±40 | V |
| Continuous Drain Current (Note 7) V _{GS} = 5V | Steady State $T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$ $T_A = +100^{\circ}C$ | | I _D | 0.23 0.18 0.14 | А |
| Maximum Continuous Body Diode Forward Current | (Note 7) | Is | 0.53 | Α | |
| Pulsed Drain Current (10µs pulse, duty cycle = 1%) | I _{DM} | 0.8 | Α | | |

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

| Characteristic | | Symbol | Value | Units | |
|--|-------------------------|----------------------------------|-------------|-------|--|
| | T _A = +25°C | | 0.31 | | |
| Total Power Dissipation (Note 6) | T _A = +70°C | P_{D} | 0.2 | W | |
| | T _A = +100°C | | 0.12 | | |
| Thermal Resistance, Junction to Ambient (Note 6) | Steady state | $R_{\theta JA}$ | 410 | °C/W | |
| | T _A = +25°C | | 0.4 | | |
| Total Power Dissipation (Note 7) | T _A = +70°C | P_{D} | 0.25 | W | |
| | T _A = +100°C | | 0.15 | | |
| Thermal Resistance, Junction to Ambient (Note 7) | Steady state | $R_{\theta JA}$ | 318 | °C/W | |
| Thermal Resistance, Junction to Case (Note 7) | Steady state | R ₀ JC | 135 | °C/W | |
| Operating and Storage Temperature Range | | T _{J,} T _{STG} | -55 to +150 | °C | |

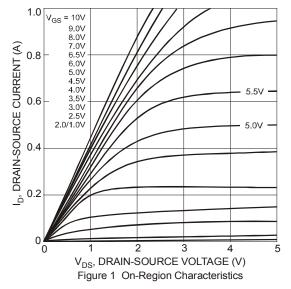
| Characteristic | | Symbol | Min | Тур | Max | Unit | Test Condition |
|------------------------------------|---|----------------------|-----|------------|-------------|------|---|
| OFF CHARACTERISTICS (Note 8) | | | | | | | |
| Drain-Source Breakdown Voltage | | BV _{DSS} | 60 | 70 | _ | V | $V_{GS} = 0V, I_D = 10\mu A$ |
| Zero Gate Voltage Drain Current | @ T _C = +25°C @ T _C = +125°C | I _{DSS} | _ | _ | 1.0 500 | μA | V _{DS} = 60V, V _{GS} = 0V |
| Gate-Body Leakage | | I _{GSS} | _ | _ | ±10 | nA | $V_{GS} = \pm 20V, V_{DS} = 0V$ |
| ON CHARACTERISTICS (Note 8) | | | | | | | _ |
| Gate Threshold Voltage | | $V_{GS(th)}$ | 1.0 | _ | 2.0 | V | $V_{DS} = V_{GS}, I_{D} = 250 \mu A$ |
| Static Drain-Source On-Resistance | @ T _J = +25°C @ T _J = +125°C | R _{DS} (ON) | _ | 3.2 4.4 | 7.5 13.5 | Ω | $V_{GS} = 5.0V, I_D = 0.05A$ $V_{GS} = 10V, I_D = 0.5A$ |
| On-State Drain Current | | I _{D(ON)} | 0.5 | 1.0 | _ | Α | V _{GS} = 10V, V _{DS} = 7.5V |
| Forward Transconductance | | g _{FS} | 80 | _ | _ | mS | V _{DS} =10V, I _D = 0.2A |
| Diode Forward Voltage | | V_{SD} | _ | 0.78 | 1.5 | V | $V_{GS} = 0V, I_S = 115mA$ |
| DYNAMIC CHARACTERISTICS (Note 9) | | | | | | | _ |
| Input Capacitance | | C _{iss} | _ | 22 | 50 | pF | V 05V V 0V |
| Output Capacitance | | Coss | _ | 11 | 25 | pF | V _{DS} = 25V, V _{GS} = 0V -f = 1.0MHz |
| Reverse Transfer Capacitance | | Crss | _ | 2.0 | 5.0 | pF | 1 - 1.0WII IZ |
| SWITCHING CHARACTERISTICS (Note 9) | | | | | | | _ |
| Turn-On Delay Time | | t _{D(on)} | _ | 7.0 | 20 | | $V_{DD} = 30V, I_D = 0.2A,$ |
| Turn-Off Delay Time | | t _{D(off)} | _ | 11.0 | 20 | ns | R_L = 150 Ω , V_{GEN} = 10 V , R_{GEN} = 25 Ω |

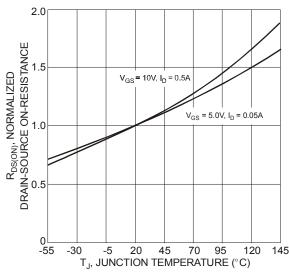
Notes:

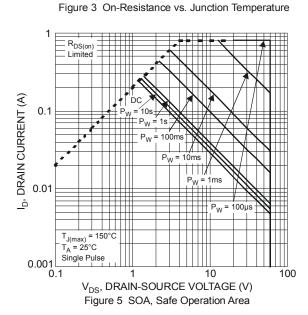
- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
- 7. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1inch square copper plate.
- 8. Short duration pulse test used to minimize self-heating effect.
- 9. Guaranteed by design. Not subject to product testing.

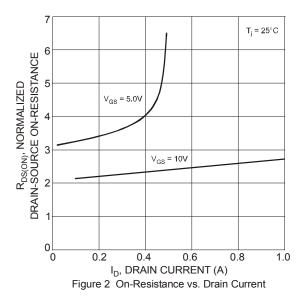


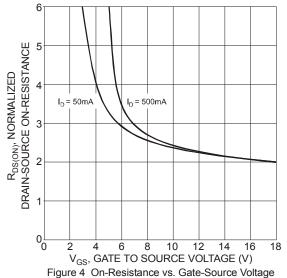
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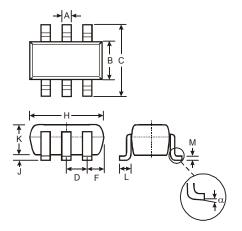
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2N7002DW

Package Outline Dimensions

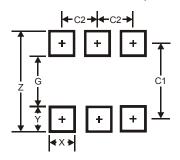
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



| SOT363 | | | | | | | |
|--------|-----------|-------|--|--|--|--|--|
| Dim | Min | Max | | | | | |
| Α | 0.10 | 0.30 | | | | | |
| В | 1.15 | 1.35 | | | | | |
| С | 2.00 | 2.20 | | | | | |
| D | 0.65 | Тур | | | | | |
| F | 0.40 | 0.45 | | | | | |
| Н | 1.80 | 2.20 | | | | | |
| J | 0 0.10 | | | | | | |
| K | 0.90 1.00 | | | | | | |
| L | 0.25 | 0.40 | | | | | |
| М | 0.10 | 0.22 | | | | | |
| α | α 0° 8° | | | | | | |
| All Di | mensions | in mm | | | | | |

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



| Dimensions | Value (in mm) |
|------------|---------------|
| Z | 2.5 |
| G | 1.3 |
| Х | 0.42 |
| Y | 0.6 |
| C1 | 1.9 |
| C2 | 0.65 |



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